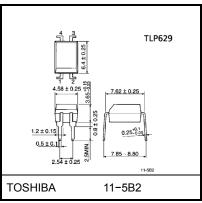
TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP629,TLP629-2,TLP629-4

Telecommunication Office Machine **Telephone Use Equipment**

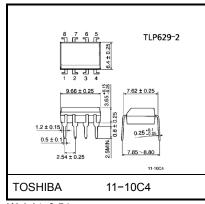
The TOSHIBA TLP629, -2, and -4 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP629-2 offers two isolated channels in an eight lead plastic DIP, while the TLP629-4 provides four isolated channels in a sixteen plastic DIP. This is suitable for application of DC input current up to 150mA.

- IF maximum rating: 150mA ٠
- Collector-emitter voltage: 55V (min.) •
- Current transfer ratio: 25% (min.) (IF=20mA) •
- Isolation voltage: 5000Vrms (min.) ٠
- UL recognized: UL1577, file no. E67349 •
- BSI approved: BS EN60065:2002, certificate no.7426 BS EN60950-1:2002, certificate no.7427

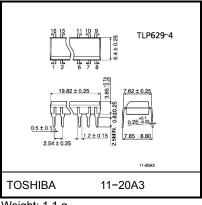


Unit in mm

Weight: 0.26 g

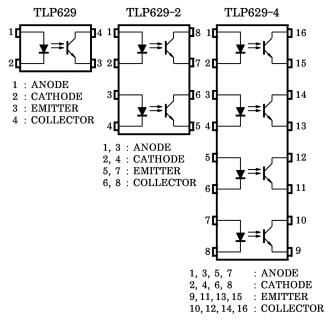


Weight: 0.54 g



Weight: 1.1 g

Pin Configurations (top view)



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Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol -	Ra	Unit	
	Characteristic		TLP629	TLP629-2,4	Unit
LED	Forward current	١ _F	150		mA
	Forward current derating	ΔI _F / °C	–1.5 (Ta ≥ 25°C)		mA / °C
	Pulse forward current	IFP	1 (100µs pulse, 100pps)		А
	Reverse voltage	V _R	5		V
	Junction temperature	Tj	125		°C
	Collector-emitter voltage	V _{CEO}	5	55	
	Emitter-collector voltage	V _{ECO}	7		V
۲	Collector current	Ι _C	80		mA
Detector	Collector power dissipation (1 circuit)	P _C	150	100	mW
	Collector power dissipation derating (1 circuit, Ta ≥ 25°C)	ΔP _C / °C	-1.5	-1.0	mW / °C
	Junction temperature	Тj	125		°C
Storage temperature range		T _{stg}	-55~125		°C
Operating temperature range		T _{opr}	-55~100		°C
Lead soldering temperature		T _{sol}	260 (10s)		°C
Total package power dissipation		Ρ _T	250	200	mW
Total package power dissipation derating (Ta≥25°C)		ΔP _T / °C	-2.5	2.0	mW / °C
Isol	ation voltage (Note 1)	BVS	5000 (AC, 1m	5000 (AC, 1min., RH ≤ 60%)	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal: LED side pins shorted together, and detector side pins shorted together.

Recommended Operating Conditions

Characteristics	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{CC}	_	5	24	V
Forward current	١ _F	_	20	120	mA
Collector current	Ι _C	_	1	10	mA
Operating temperature	T _{opr}	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	VF	I _F = 100 mA	_	1.4	1.7	V
	Forward current	١ _F	V _F = 0.7 V	-	2.5	20	μA
Ш	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	50	_	pF
Detector	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	55	_	_	V
	Emitter–collector breakdown voltage	V _{(BR) ECO}	I _E = 0.1 mA	7	_	_	V
	Collector dark current	ICEO	V _{CE} = 24 V	_	10	100	nA
			V _{CE} = 24 V, Ta = 85°C	_	2	50	μA
	Capacitance collector to emitter	C _{CE}	V = 0, f = 1 MHz	_	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Mln.	Тур.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 20 mA, V _{CE} = 1 V	25	_	_	
	I _C / I _F (high)	I _F = 100 mA, V _{CE} = 1 V	20	_	80	%
Collector-emitter saturation voltage	VCE (sat)	I _C = 2.4 mA, I _F = 20 mA	_	_	0.4	v
		I _C = 2.4 mA, I _F = 100 mA	—	_	0.4	v
Off-state collector current	I _{C(off)}	V _F = 0.7V, V _{CEO} = 24 V		1	1.0	μA

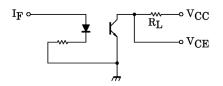
Isolation Characteristics (Ta = 25°C)

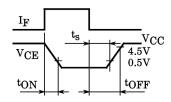
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V	5×10 ¹⁰	10 ¹⁴	_	Ω
		AC, 1 minute	5000	_	_	V
Isolation voltage	BVS	AC, 1 second, in oil	_	10000	_	V _{rms}
		DC, 1 minute, in oil		10000		Vdc

Switching Characteristics (Ta = 25°C)

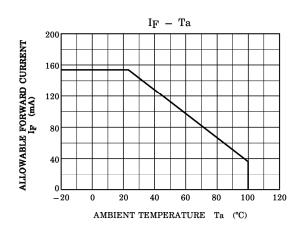
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	tr		_	2	_	
Fall time	t _f	V _{CC} = 10 V, I _C = 2 mA	_	3	_	
Turn–on time	t _{on}	R _L = 100Ω	_	3	10	μs
Turn-off time	t _{off}		_	3	10	
Turn–on time	t _{ON}		_	2	_	
Storage time	ts	R_L = 1.9 kΩ (Fig.1) V _{CC} = 5 V, I _F = 16 mA	_	15	_	μs
Turn–off time	tOFF		_	25	_	

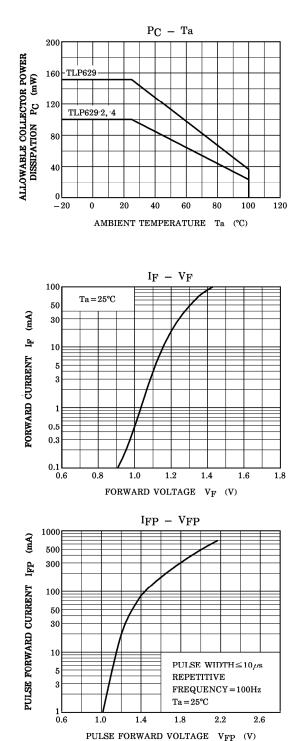
Fig. 1 Switching time test circuit

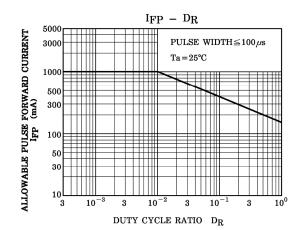


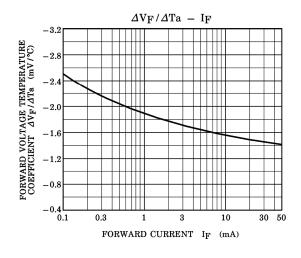


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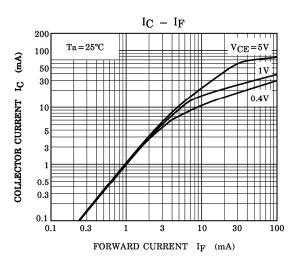


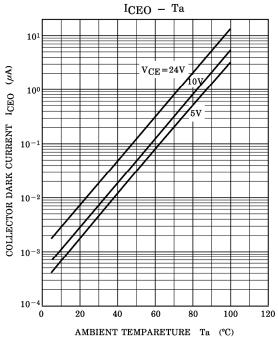


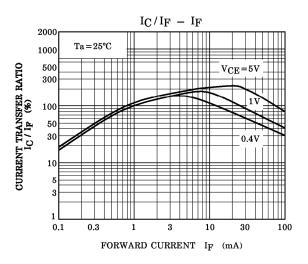




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